

FEATURES

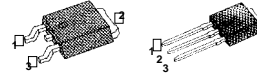
- ◆ Avalanche Rugged Technology
- ◆ Rugged Gate Oxide Technology
- ◆ Lower Input Capacitance
- ◆ Improved Gate Charge
- ◆ Extended Safe Operating Area
- ◆ Lower Leakage Current: 10µA (Max.) @ $V_{DS} = 100V$
- ◆ Lower $R_{DS(ON)}$: 0.336Ω (Typ.)

$$BV_{DSS} = 100 V$$

$$R_{DS(on)} = 0.44\Omega$$

$$I_D = 4.7 A$$

D-PAK **I-PAK**



1. Gate 2. Drain 3. Source

Absolute Maximum Ratings

| Symbol | Characteristic | Value | Units |
|----------------|---|--------------|---------------|
| V_{DSS} | Drain-to-Source Voltage | 100 | V |
| I_D | Continuous Drain Current ($T_C=25^\circ C$) | 4.7 | A |
| | Continuous Drain Current ($T_C=100^\circ C$) | 3 | |
| I_{DM} | Drain Current-Pulsed (1) | 16 | A |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulsed Avalanche Energy (2) | 58 | mJ |
| I_{AR} | Avalanche Current (1) | 4.7 | A |
| E_{AR} | Repetitive Avalanche Energy (1) | 2.2 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (3) | 6.5 | V/ns |
| P_D | Total Power Dissipation ($T_A=25^\circ C$) * | 2.5 | W |
| | Total Power Dissipation ($T_C=25^\circ C$) | 22 | W |
| | Linear Derating Factor | 0.18 | W/ $^\circ C$ |
| T_J, T_{STG} | Operating Junction and Storage Temperature Range | - 55 to +150 | $^\circ C$ |
| T_L | Maximum Lead Temp. for Soldering Purposes, 1/8. from case for 5-seconds | 300 | |

Thermal Resistance

| Symbol | Characteristic | Typ. | Max. | Units |
|-----------------|-----------------------|------|------|--------------|
| $R_{\theta JC}$ | Junction-to-Case | -- | 5.6 | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction-to-Ambient * | -- | 50 | |
| $R_{\theta JA}$ | Junction-to-Ambient | -- | 110 | |

* When mounted on the minimum pad size recommended (PCB Mount).

Rev. B

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Electrical Characteristics (T_C=25°C unless otherwise specified)

| Symbol | Characteristic | Min. | Typ. | Max. | Units | Test Condition |
|---------------------|---|------|------|------|-------|---|
| BV _{DSS} | Drain-Source Breakdown Voltage | 100 | -- | -- | V | V _{GS} =0V, I _D =250μA |
| ΔBV/ΔT _J | Breakdown Voltage Temp. Coeff. | -- | 0.1 | -- | V/°C | I _D =250μA See Fig 7 |
| V _{GS(th)} | Gate Threshold Voltage | 1.0 | -- | 2.0 | V | V _{DS} =5V, I _D =250μA |
| I _{GSS} | Gate-Source Leakage, Forward | -- | -- | 100 | nA | V _{GS} =20V |
| | Gate-Source Leakage, Reverse | -- | -- | -100 | | V _{GS} =-20V |
| I _{DSS} | Drain-to-Source Leakage Current | -- | -- | 10 | μA | V _{DS} =100V |
| | | -- | -- | 100 | | V _{DS} =80V, T _C =125°C |
| R _{DS(on)} | Static Drain-Source On-State Resistance | -- | -- | 0.44 | Ω | V _{GS} =5V, I _D =2.35A (4) |
| g _{fs} | Forward Transconductance | -- | 3.2 | -- | Ω | V _{DS} =40V, I _D =2.35A (4) |
| C _{iss} | Input Capacitance | -- | 180 | 235 | pF | V _{GS} =0V, V _{DS} =25V, f=1MHz See Fig 5 |
| C _{oss} | Output Capacitance | -- | 50 | 65 | | |
| C _{rss} | Reverse Transfer Capacitance | -- | 20 | 25 | | |
| t _{d(on)} | Turn-On Delay Time | -- | 8 | 25 | ns | V _{DD} =50V, I _D =5.6A, R _G =12Ω See Fig 13 (4) (5) |
| t _r | Rise Time | -- | 10 | 30 | | |
| t _{d(off)} | Turn-Off Delay Time | -- | 17 | 45 | | |
| t _f | Fall Time | -- | 8 | 25 | | |
| Q _g | Total Gate Charge | -- | 5.5 | 8 | nC | V _{DS} =80V, V _{GS} =5V, I _D =5.6A See Fig 6 & Fig 12 (4) (5) |
| Q _{gs} | Gate-Source Charge | -- | 0.9 | -- | | |
| Q _{gd} | Gate-Drain (. Miller.) Charge | -- | 3.5 | -- | | |

Source-Drain Diode Ratings and Characteristics

| Symbol | Characteristic | Min. | Typ. | Max. | Units | Test Condition |
|-----------------|---------------------------|------|------|------|-------|---|
| I _S | Continuous Source Current | -- | -- | 4.7 | A | Integral reverse pn-diode in the MOSFET |
| I _{SM} | Pulsed-Source Current (1) | -- | -- | 16 | | |
| V _{SD} | Diode Forward Voltage (4) | -- | -- | 1.5 | V | T _J =25°C, I _S =4.7A, V _{GS} =0V |
| t _{rr} | Reverse Recovery Time | -- | 85 | -- | ns | T _J =25°C, I _F =5.6A |
| Q _{rr} | Reverse Recovery Charge | -- | 0.23 | -- | μC | di _F /dt=100A/μs (4) |

Notes;

- (1) Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- (2) L=4mH, I_{AS}=4.7A, V_{DD}=25V, R_G=27Ω, Starting T_J=25°C
- (3) I_{SD} ≤ 5.6A, di/dt ≤ 250A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J=25°C
- (4) Pulse Test: Pulse Width = 250μs, Duty Cycle ≤ 2%
- (5) Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

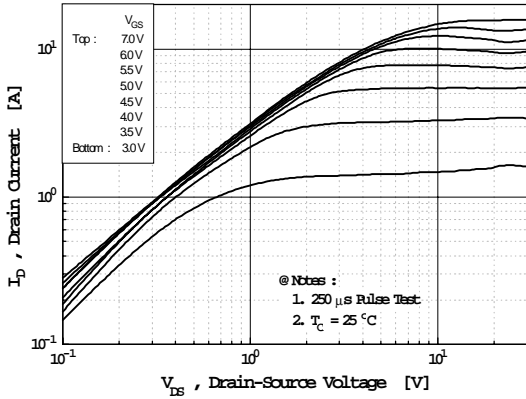


Fig 2. Transfer Characteristics

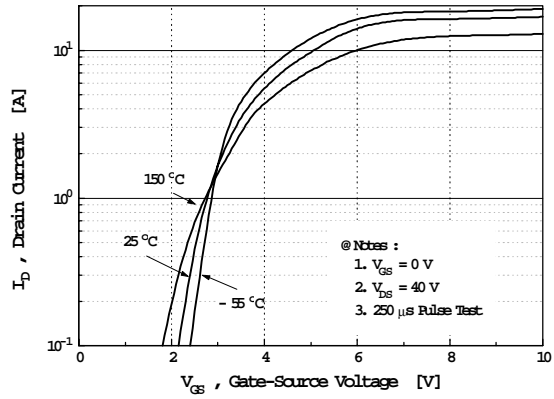


Fig 3. On-Resistance vs. Drain Current

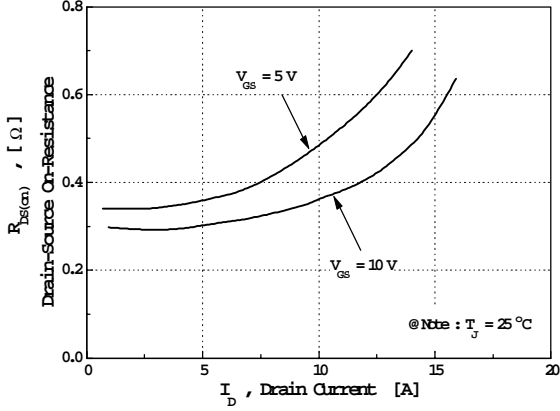


Fig 4. Source-Drain Diode Forward Voltage

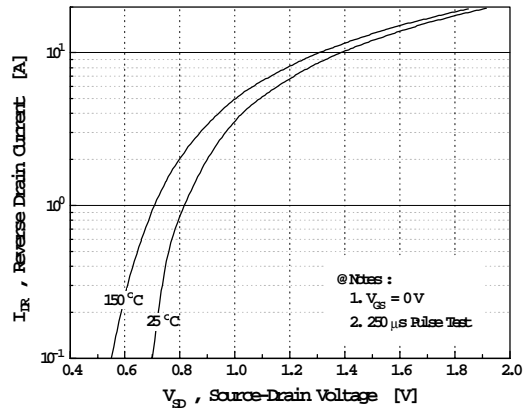


Fig 5. Capacitance vs. Drain-Source Voltage

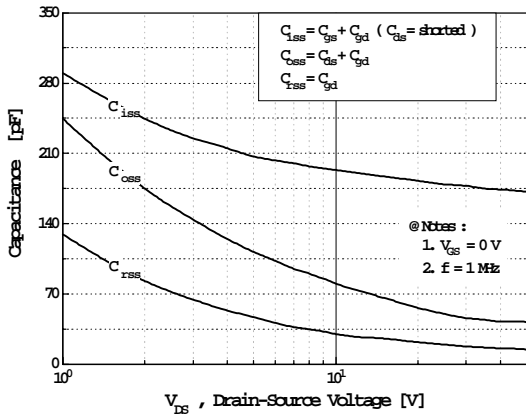


Fig 6. Gate Charge vs. Gate-Source Voltage

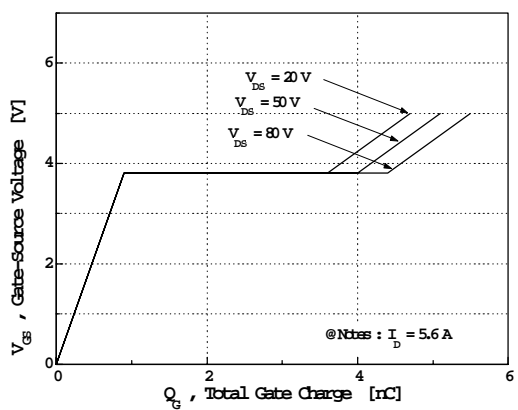


Fig 7. Breakdown Voltage vs. Temperature

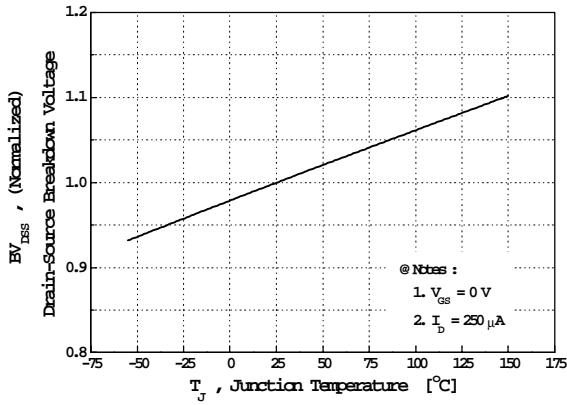


Fig 8. On-Resistance vs. Temperature

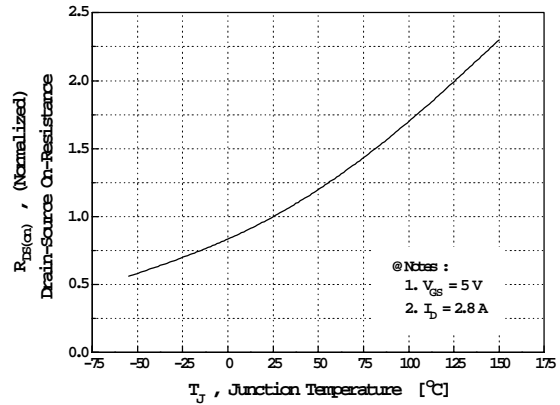


Fig 9. Max. Safe Operating Area

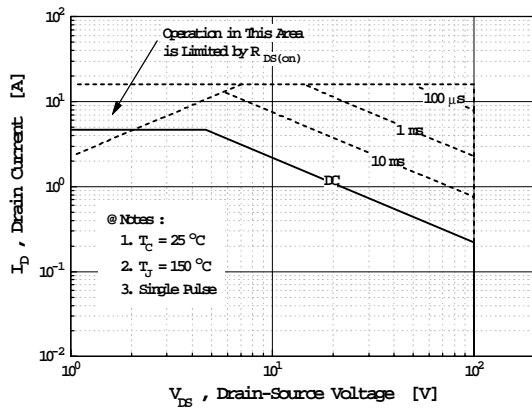


Fig 10. Max. Drain Current vs. Case Temperature

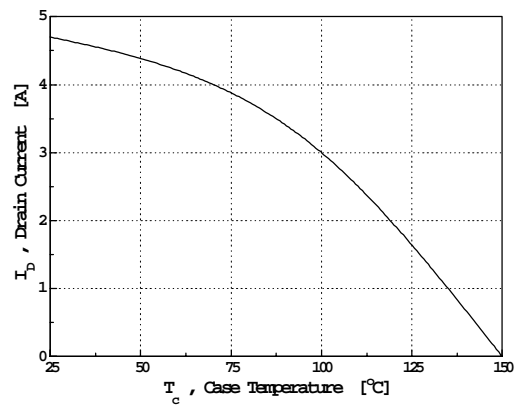


Fig 11. Thermal Response

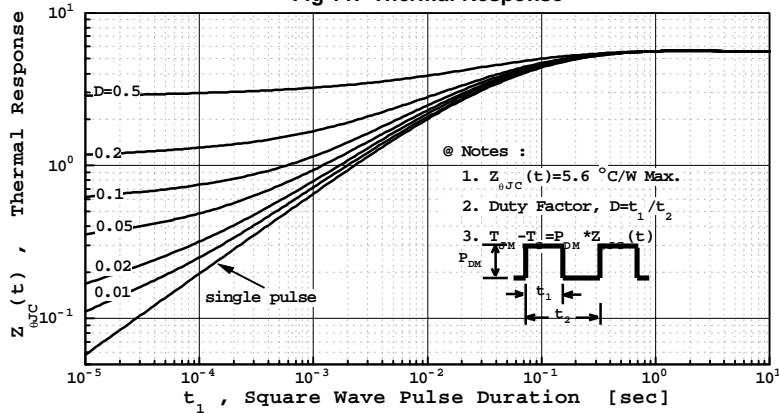


Fig 12. Gate Charge Test Circuit & Waveform

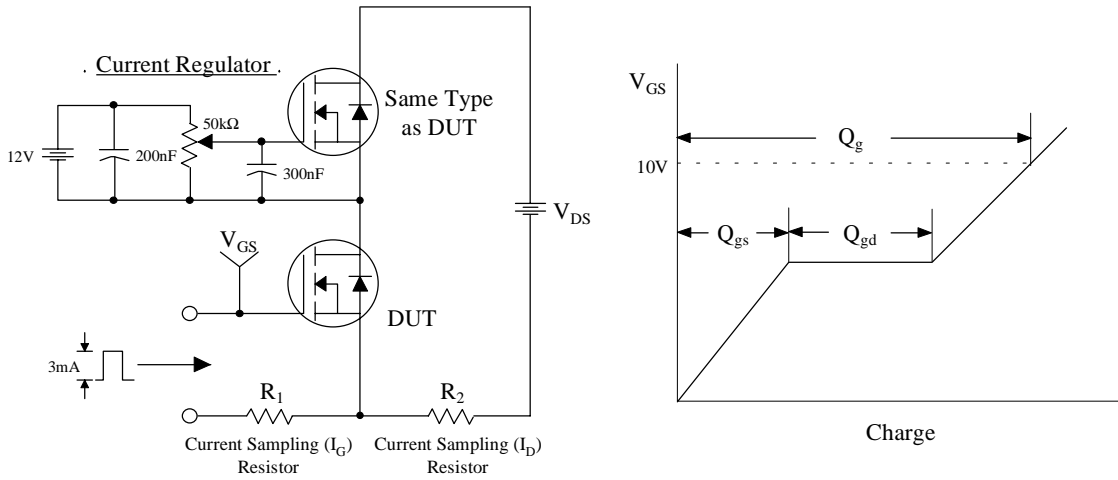


Fig 13. Resistive Switching Test Circuit & Waveforms

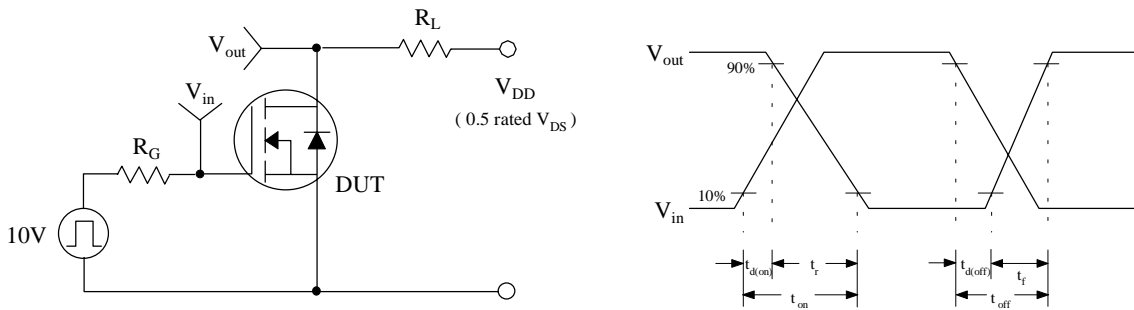


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

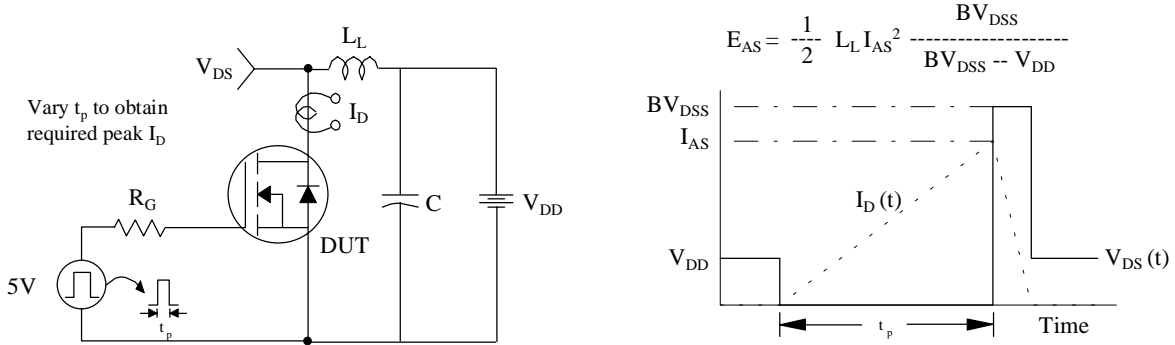
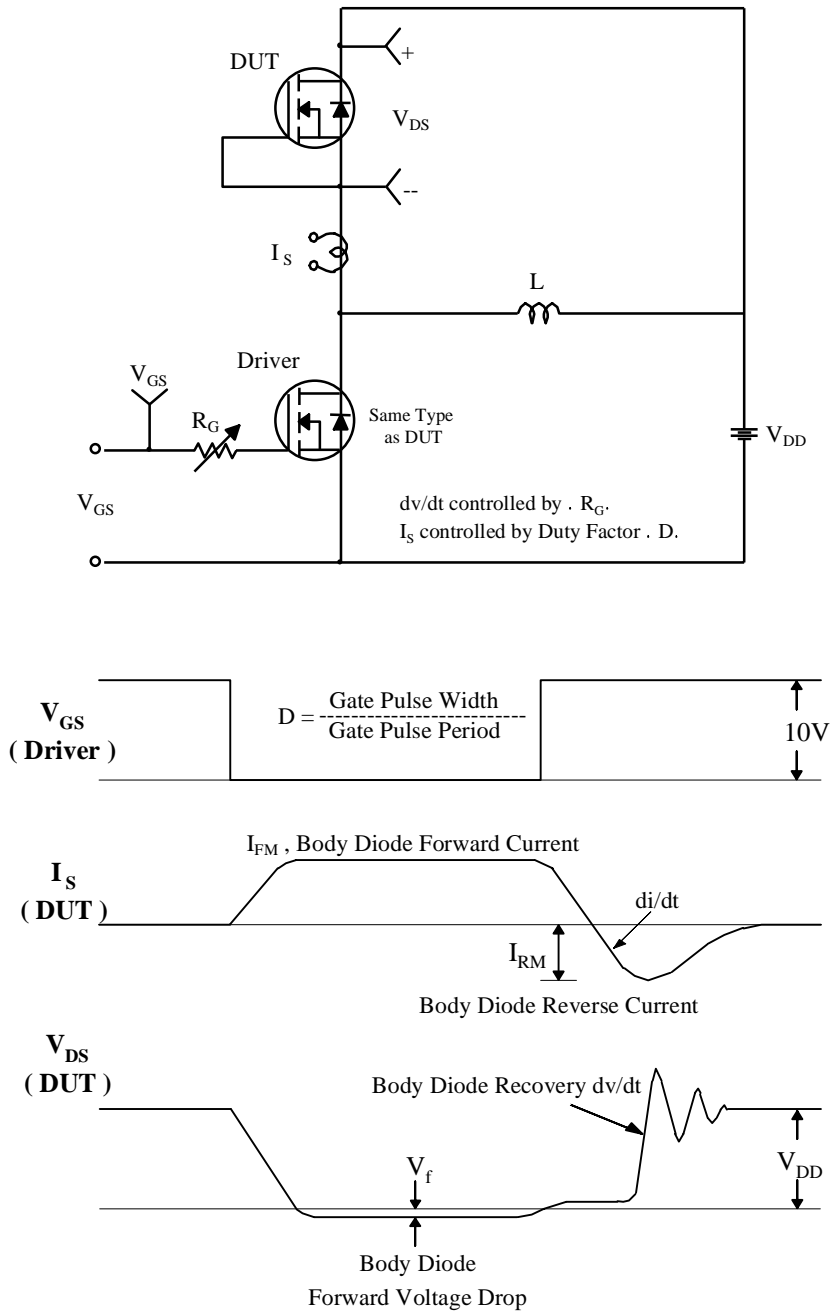


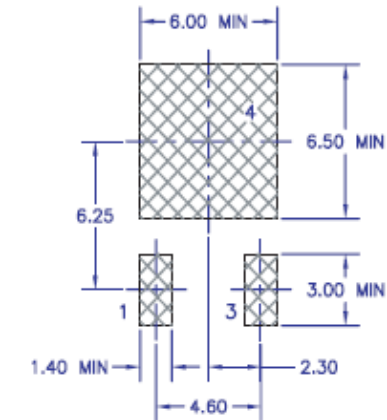
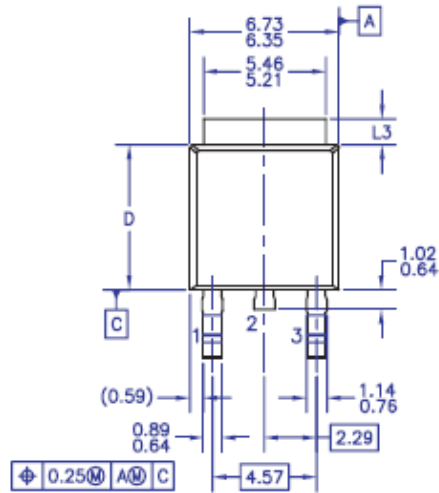
Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



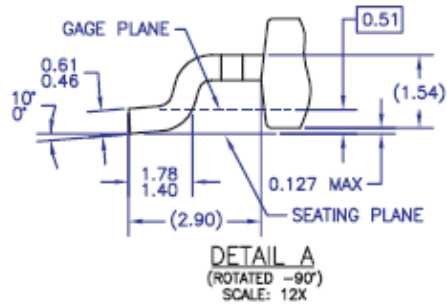
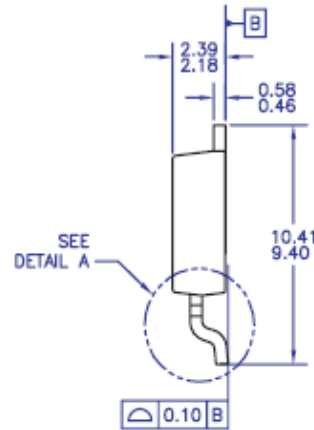
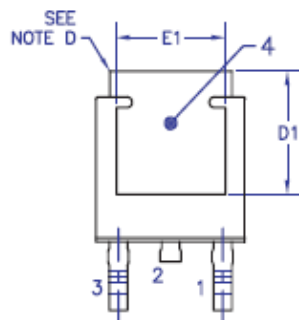
DPAK Package Dimensions



D - PAK



LAND PATTERN RECOMMENDATION



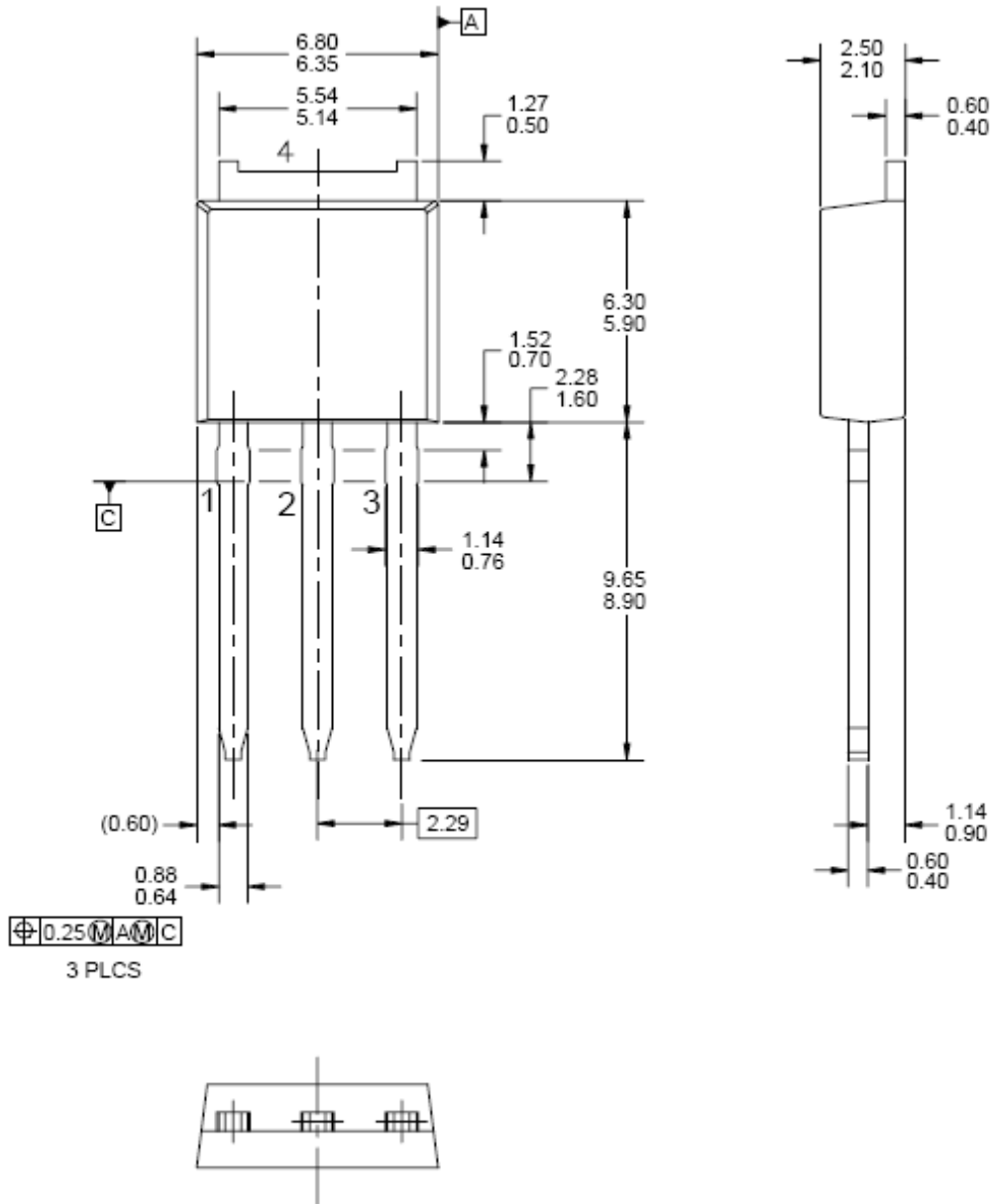
Dimensions in Millimeters

September 1999, Rev B

I-PAK Package Dimensions



I - PAK



Dimensions in Millimeters

September 1999, Rev B

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